Band switching diode

1SS356

●Applications

High frequency switching

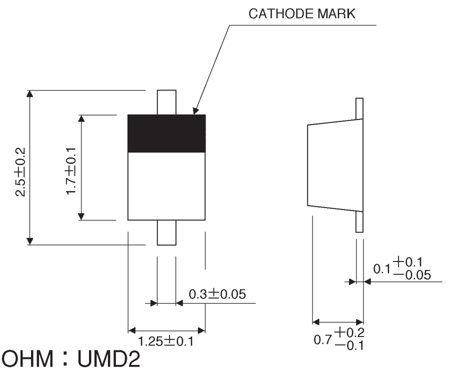
●Features

1) Small surface mounting type. (UMD2)
2) High reliability.

●Construction

Silicon epitaxial planar

●External dimensions (Units: mm)



ROHM：UMD2
EIAJ：SC - 76
JEDEC：SOD - 323

●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
DC reverse voltage	V_R	35	V
DC forward current	I_F	100	mA
Junction temperature	Tj	125	℃
Storage temperature	Tstg	－55～＋125	℃

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	－	0.83	1.0	V	I_F＝10mA
Reverse current	I_R	－	0.01	10	nA	V_R＝25V
Capacitance between terminals	C_T	－	0.80	1.2	pF	V_R＝6V，f＝1MHz
Forward operating resistance	r_F	－	0.62	0.9	Ω	I_F＝2mA，f＝100MHz

●Electrical characteristic curves (Ta = 25°C unless specified otherwise)

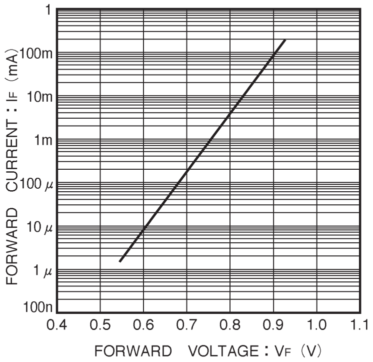


Fig. 1 Forward characteristics

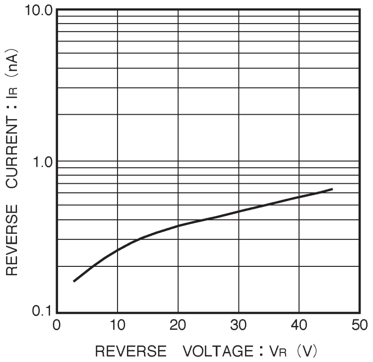


Fig. 2 Reverse characteristics

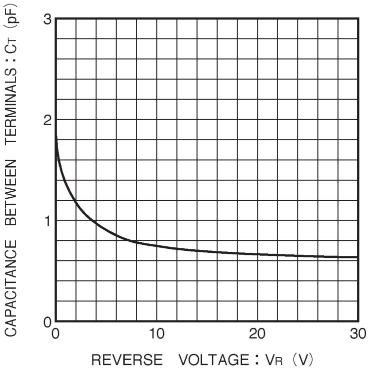


Fig. 3 Capacitance between terminals characteristics

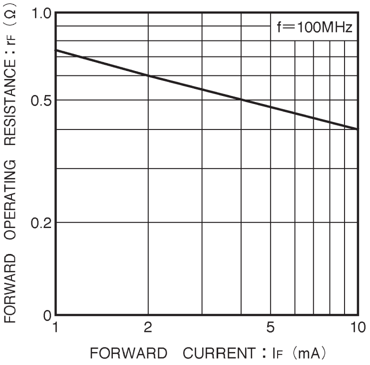


Fig. 4 Forward operating resistance characteristics

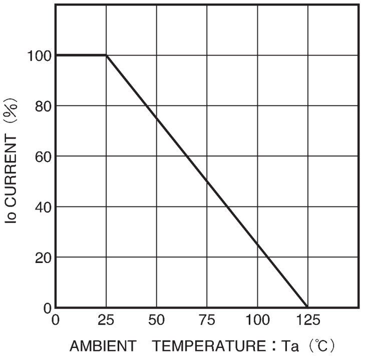


Fig. 5 Derating curve (mounting on glass epoxy PCBs)